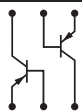


CMXT3906

**SURFACE MOUNT
DUAL PNP
SILICON TRANSISTORS**

SUPERmini™



SOT-26 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXT3906 type is a dual PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, and designed for small signal general purpose amplifier and switching applications.

MARKING CODE: X2A

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{CBO} 40
 V_{CEO} 40
 V_{EBO} 5.0
 I_C 200
 P_D 350
 T_J, T_{stg} -65 to +150
 θ_{JA} 357

UNITS

V
V
V
mA
mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CEV}	$V_{CE}=30\text{V}, V_{EB}=3.0\text{V}$		50	nA
BV_{CBO}	$I_C=10\mu\text{A}$	40		V
BV_{CEO}	$I_C=1.0\text{mA}$	40		V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.25	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.40	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	0.65	0.85	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.95	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=0.1\text{mA}$	60		
h_{FE}	$V_{CE}=1.0\text{V}, I_C=1.0\text{mA}$	80		
h_{FE}	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	100	300	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=50\text{mA}$	60		
h_{FE}	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	30		
f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	250		MHz
C_{ob}	$V_{CB}=5.0\text{V}, I_E=0, f=1.0\text{MHz}$		4.5	pF
C_{ib}	$V_{BE}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$		10	pF
h_{ie}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	2.0	12	k Ω

R3 (12-February 2010)

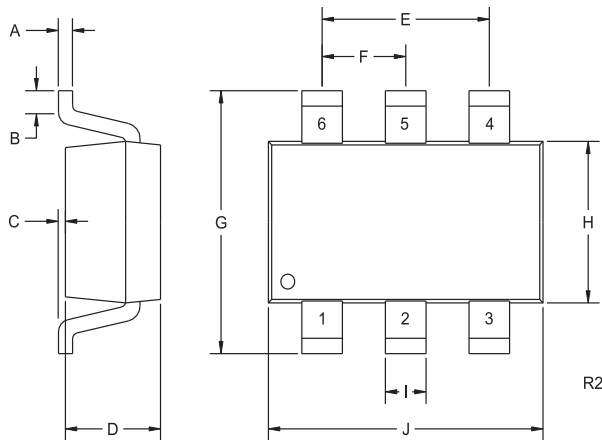
CMXT3906
SURFACE MOUNT
DUAL PNP
SILICON TRANSISTORS



ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

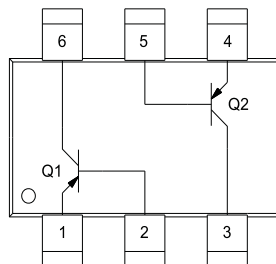
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{re}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	0.1	10	$\times 10^{-4}$
h_{fe}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	100	400	
h_{oe}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	3.0	60	μS
NF	$V_{CE}=5.0\text{V}$, $I_C=100\mu\text{A}$, $R_S=1.0\text{k}\Omega$, $f=10\text{Hz}$ to 15.7kHz		4.0	dB
t_d	$V_{CC}=3.0\text{V}$, $V_{BE}=0.5\text{V}$, $I_C=10\text{mA}$, $I_{B1}=1.0\text{mA}$		35	ns
t_r	$V_{CC}=3.0\text{V}$, $V_{BE}=0.5\text{V}$, $I_C=10\text{mA}$, $I_{B1}=1.0\text{mA}$		35	ns
t_s	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$		225	ns
t_f	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$		75	ns

SOT-26 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016		0.41	
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)



LEAD CODE:

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

MARKING CODE: X2A

R3 (12-February 2010)